1. General description

PNP/PNP matched double transistors in an ultra small DFN1010B-6 (SOT1216) leadless Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: BCM847QAS

2. Features and benefits

- · Reduces component count
- Reduces pick and place costs
- Low package height of 0.37 mm
- · Current gain matching
- · Base-emitter voltage matching
- Application-optimized pinout
- AEC-Q101 qualified

3. Applications

- Current mirror
- Differential amplifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor	Per transistor							
V _{CEO}	collector-emitter voltage	open base		-	-	-45	V	
I _C	collector current			-	-	-100	mA	
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-	-200	mA	
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		200	290	450		
Per device								
h _{FE1} /h _{FE2}	DC current gain matching	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		0.95	1	1.05		
V _{BE1} -V _{BE2}	base-emitter voltage matching		[1]	-	-	2	mV	

^[1] The smaller of the two values is subtracted from the larger value.



45 V, 100 mA PNP/PNP matched double transistors

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E1	emitter TR1		6 5 4
2	B1	base TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \end{bmatrix}$	
3	C2	collector TR2	2 5	(TR1) TR2)
4	E2	emitter TR2		
5	B2	base TR2	3 0 4	1 2 3
6	C1	collector TR1	Transparent top view	sym018
7	C1	collector TR1	Transparent top view DFN1010B-6 (SOT1216)	
8	C2	collector TR2	,	

6. Ordering information

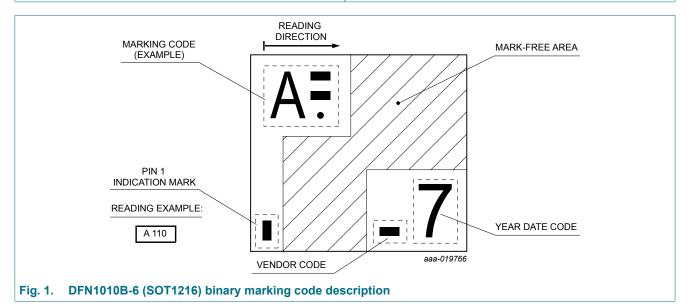
Table 3. Ordering information

Type number Package					
	Name	Description	Version		
BCM857QAS	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

7. Marking

Table 4. Marking codes

Type number	Marking code
BCM857QAS	C 011



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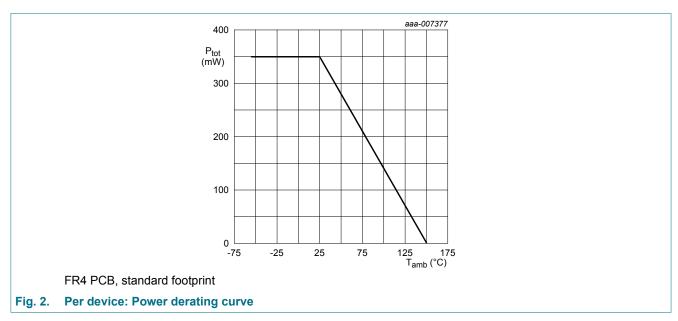
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transist	or		,			'
V _{CBO}	collector-base voltage	open emitter		-	-50	V
V _{CEO}	collector-emitter voltage	open base		-	-45	V
V _{EBO}	emitter-base voltage	open collector		-	-6	V
I _C	collector current			-	-100	mA
I _{CM}	peak collector current	t _p ≤ 1 ms; single pulse		-	-200	mA
I _{BM}	peak base current			-	-100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	230	mW
Per device			·			
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	350	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.



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9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	r		·				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	544	K/W
Per device			,				
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	358	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

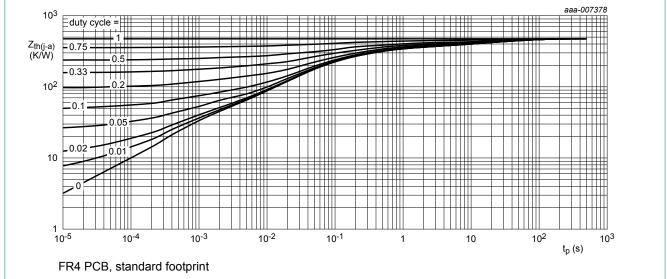


Fig. 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

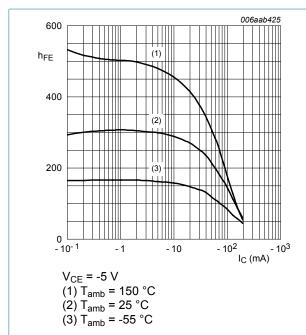
Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transisto	or						
V _{(BR)CBO}	collector-base breakdown voltage	I _C = -100 μA; I _E = 0 A		-50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = -2 mA; I _B = 0 A		-45	-	-	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	I _C = 0 A; I _E = -100 μA		-6	-	-	V
I _{CBO}	collector-base cut-off	V _{CB} = -30 V; I _E = 0 A; T _{amb} = 25 °C		-	-	-15	nA
	current	V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C		-	-	-5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	-100	nA
h _{FE}	DC current gain	V_{CE} = -5 V; I_{C} = -10 μ A; T_{amb} = 25 °C		-	250	-	
		V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		200	290	450	
V _{CEsat}	CEsat collector-emitter saturation voltage	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C		-	-	-200	mV
		I_C = -100 mA; I_B = -5 mA; T_{amb} = 25 °C	[1]	-	-	-400	mV
V _{BEsat}	base-emitter saturation	I_C = -10 mA; I_B = -0.5 mA; T_{amb} = 25 °C	[2]	-	-760	-	mV
	voltage	I_C = -100 mA; I_B = -5 mA; T_{amb} = 25 °C	[2]	-	-900	-	mV
V_{BE}	base-emitter voltage	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C	[3]	-600	-660	-725	mV
		V_{CE} = -5 V; I_{C} = -10 mA; T_{amb} = 25 °C	[3]	-	-710	-820	mV
C _c	collector capacitance	V_{CB} = -10 V; I_E = 0 A; i_e = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	-	4	pF
C _e	emitter capacitance	V_{EB} = -0.5 V; I_{C} = 0 A; f = 1 MHz; T_{amb} = 25 °C		-	10	-	pF
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C		100	175	-	MHz
Per device	·			•			•
h _{FE1} /h _{FE2}	DC current gain matching	V_{CE} = -5 V; I_{C} = -2 mA; T_{amb} = 25 °C		0.95	1	1.05	
V _{BE1} -V _{BE2}	base-emitter voltage matching		[4]	-	-	2	mV
		1	1		1	1	

Pulse test: $t_p \le 300~\mu s$; $\delta \le 0.02$ V_{BEsat} decreases by about 1.7 mV/K with increasing temperature. V_{BE} decreases by about 2 mV/K with increasing temperature. The smaller of the two values is subtracted from the larger value.

^[2] [3] [4]

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DC current gain as a function of collector Fig. 4. current; typical values

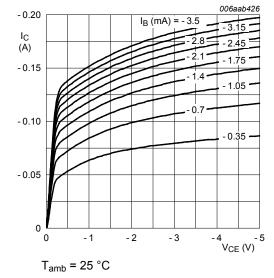


Fig. 5. Collector current as a function of collectoremitter voltage; typical values

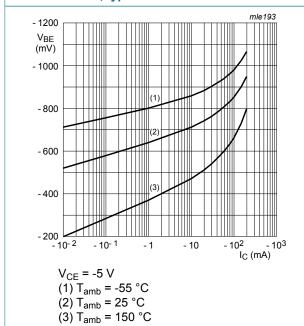
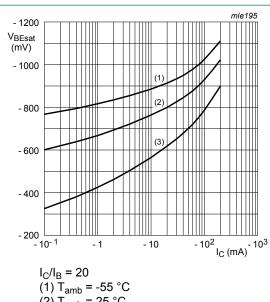


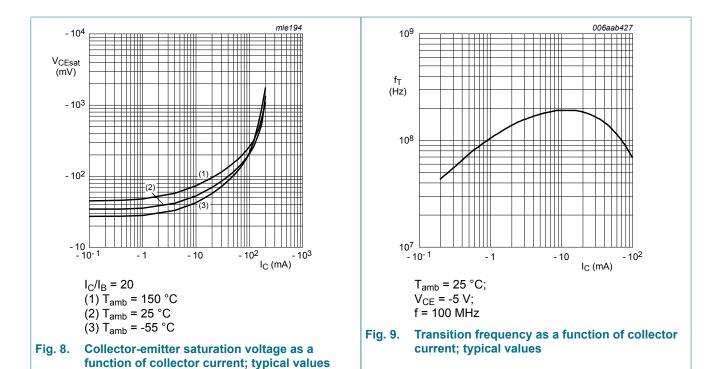
Fig. 6. Base-emitter voltage as a function of collector current; typical values



(2) T_{amb} = 25 °C (3) $T_{amb} = 150 \, ^{\circ}C$

Fig. 7. Base-emitter saturation voltage as a function of collector current; typical values

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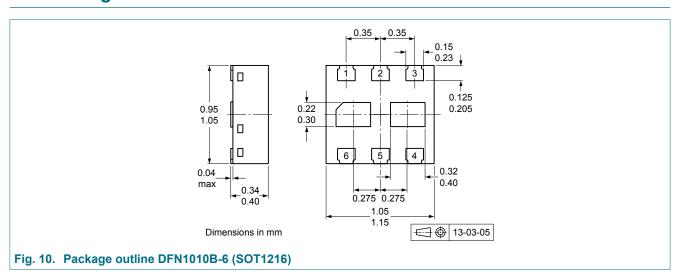


11. Test information

Quality information

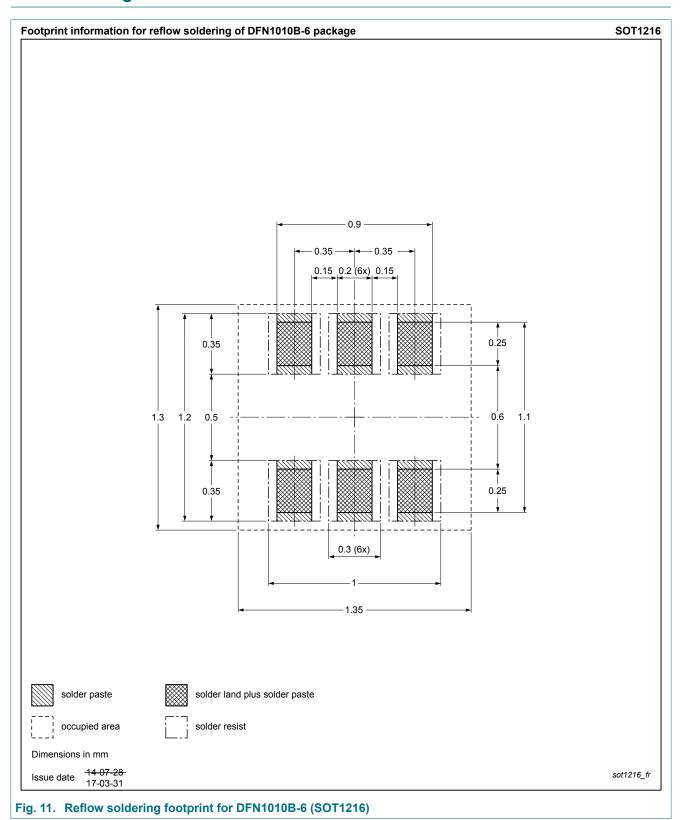
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
BCM857QAS v.1	20180424	Product data sheet	-	-

for the products described herein shall be limited

Data sheet status

15. Legal information

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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